

# Upgrades of CMS inner tracker for HL-LHC (pixels)

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# Introduction

- CMS pixel phase-II upgrade motivations
- Detector operating conditions
- Detector layout choices
- Readout chip specifications
- Possible sensor choices
- Conclusions





- **CMS pixel phase-II upgrade motivations**

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# Phase II upgrade motivations

Major achievement of LHC: Higgs discovery in 2012!

That's not the whole story, are other questions that need to be answered

- Need to investigate the entire Higgs sector

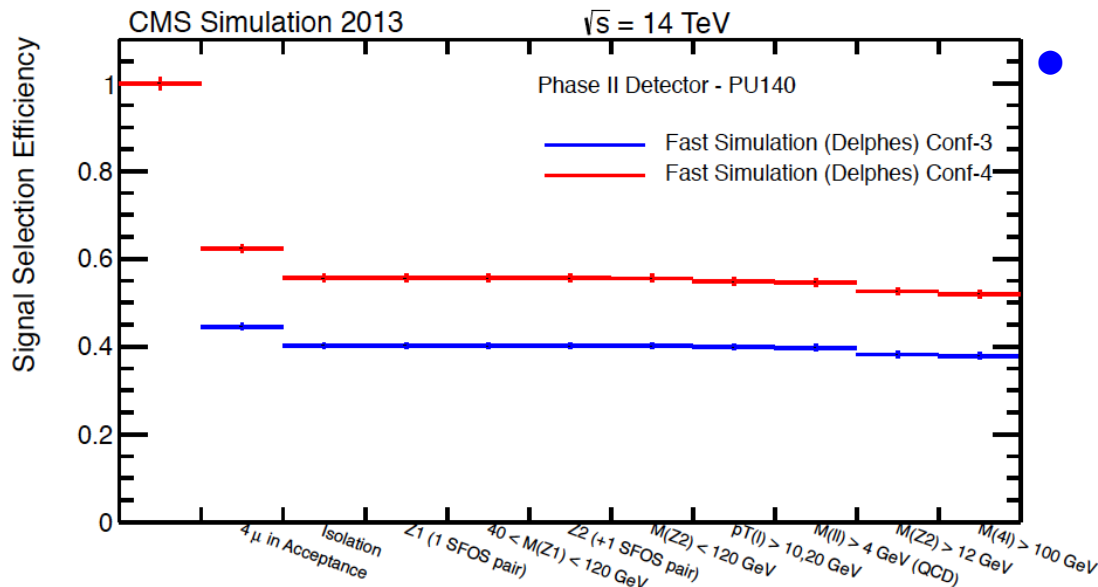
- Higgs coupling and property measurements;
- Di-Higgs searches with the aim of Higgs self coupling measurement;
- Vector Boson Scattering (VBS) measurements (crucial forward tagging jets).

- Standard Model (SM) measurements

- Precision measurements (e.g.  $M_W, \sin\theta_W, \alpha_s$ )
- Search for rare SM processes, enhanced by BSM (e.g.  $B_{s,d} \rightarrow \mu\mu$ )
- Differential measurements of W, Z, di-boson, Top

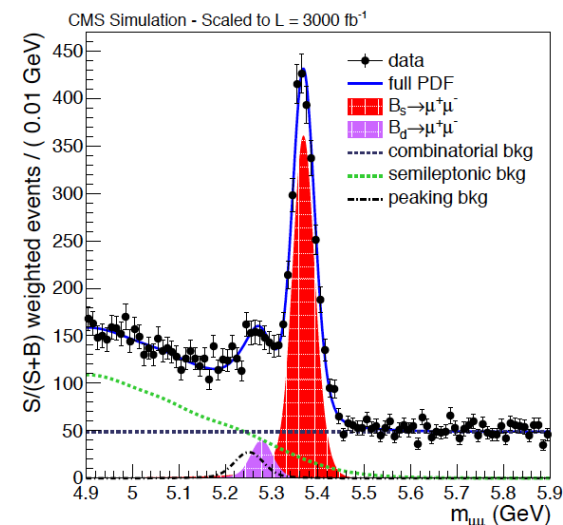
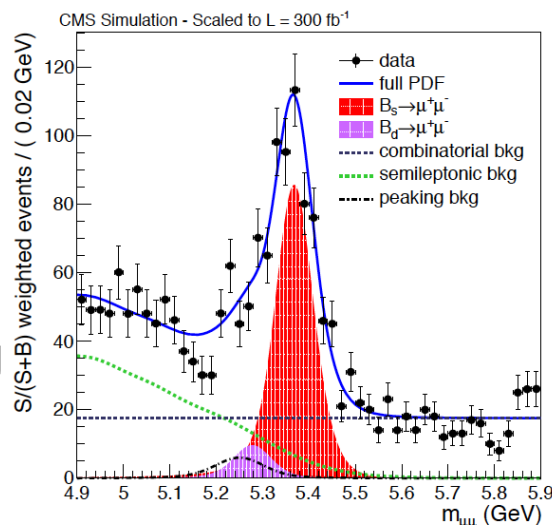
Luminosity	300/fb	3000/fb
<b>Coupling parameter</b>	7-parameter fit	
$k_Y$	5-7%	2-5%
$k_g$	6-8%	3-5%
$k_W$	4-6%	2-5%
$k_Z$	4-6%	2-4%
$k_u$	14-15%	7-10%
$k_d$	10-13%	4-7%
$k_l$	6-8%	2-5%
$\Gamma_H$	12-15%	5-8%

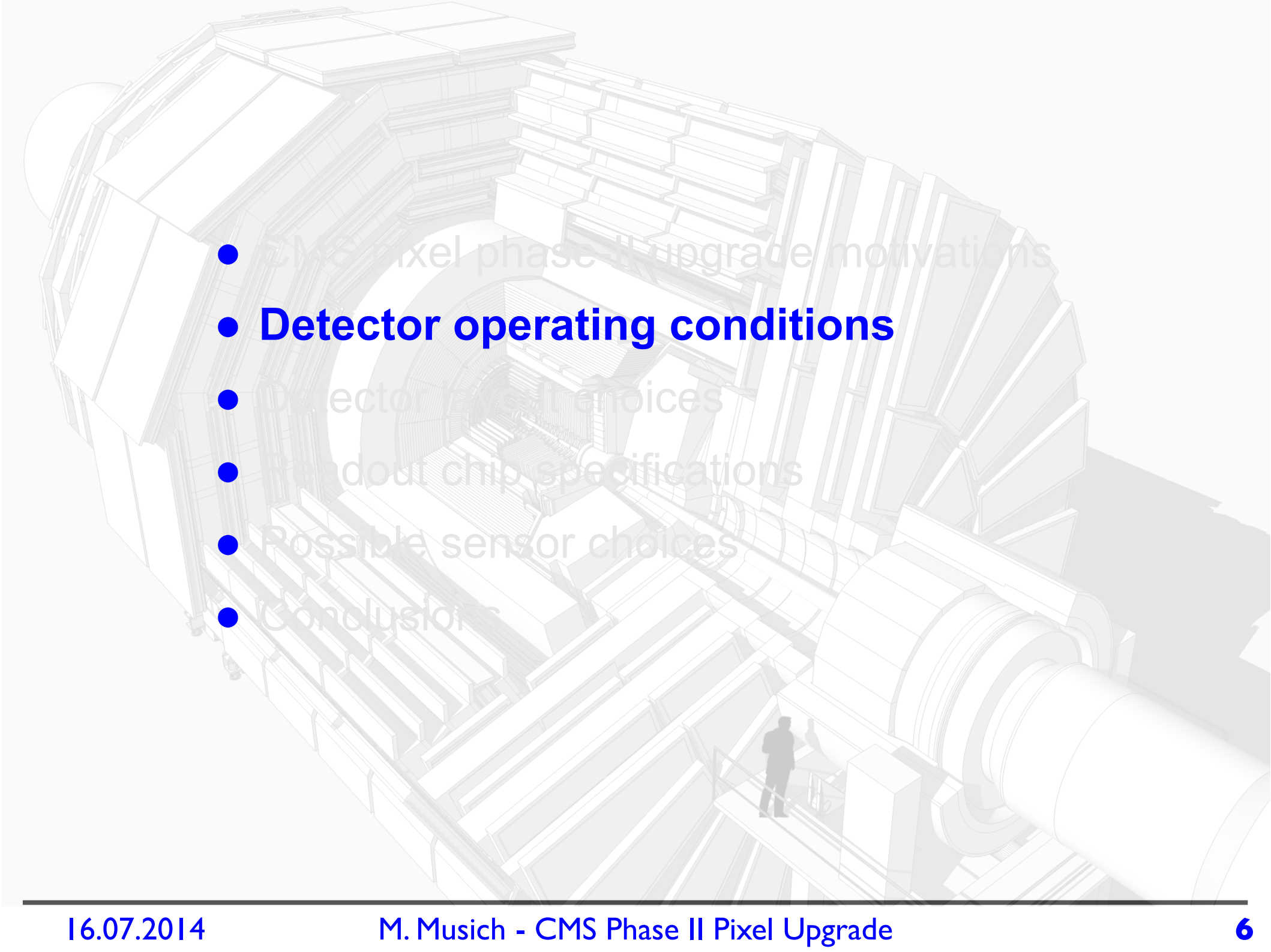
# Phase II upgrade, some motivations



- Efficiency cut flow for  $H \rightarrow ZZ \rightarrow \mu\mu\mu\mu$ 
  - Conf-3: sub-detectors have same angular acceptance as current version, but central tracking detector and the forward electromagnetic calorimeters are replaced and improved
  - Conf-4: tracking, electromagnetic and hadronic calorimetry, and muon detector, are increased in acceptance up to  $\eta \sim 4$ .

- $B_{s/d} \rightarrow \mu\mu$  mass resolution for 300/fb and 3000/fb
  - Improvement in mass resolution for the 3000/fb projection expected from *improved inner tracking system* and by removing end-cap candidates



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# HL – LHC environment

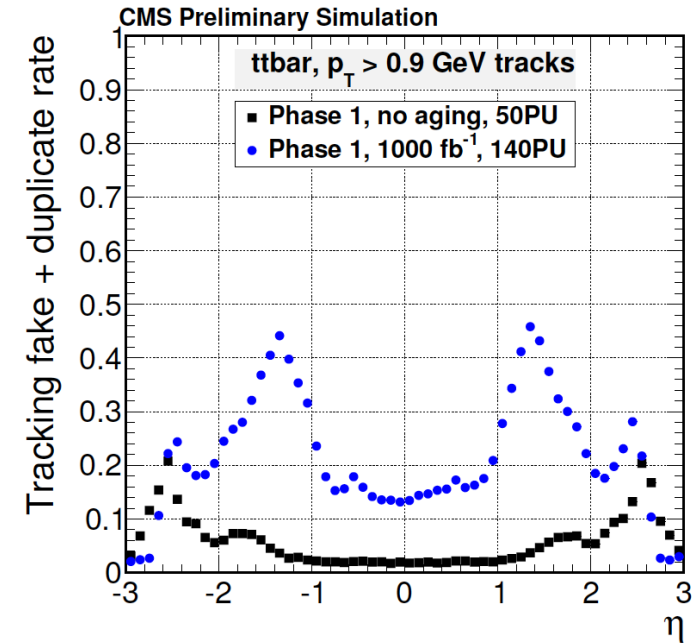
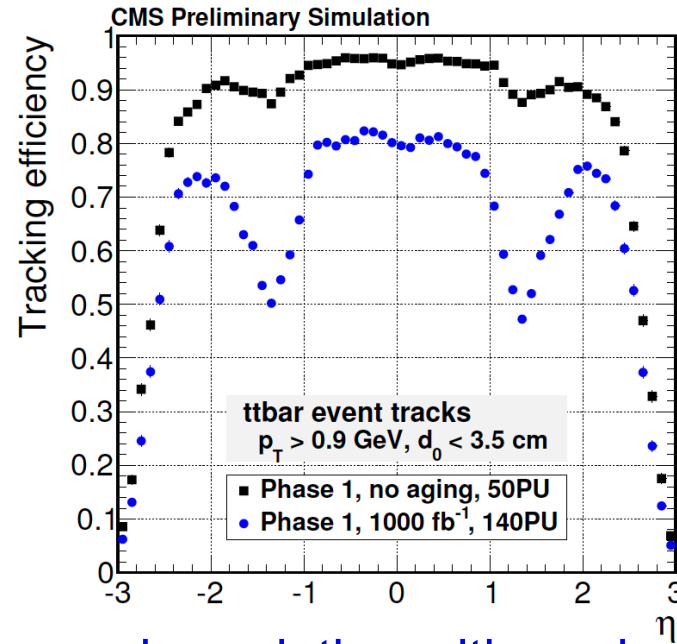
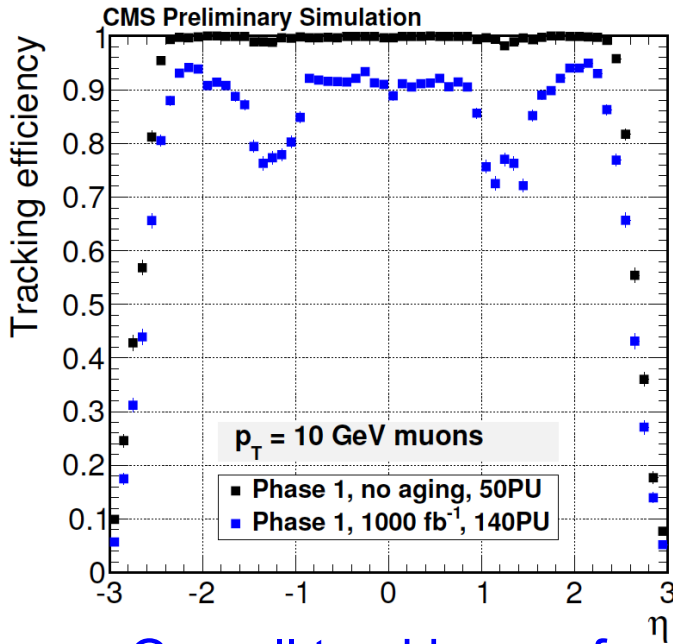
LHC												HL-LHC							
<b>Run1</b> 8x10 <sup>34</sup> s <sup>-1</sup> cm <sup>-2</sup> 30/fb E=7-8 TeV BX=50ns <PU>~20-30			<b>LS1</b>			<b>Run2</b> 2x10 <sup>34</sup> s <sup>-1</sup> cm <sup>-2</sup> 300/fb E=13-14 TeV BX=25ns <PU>~50			<b>LS2</b>			<b>Run3</b> 2x10 <sup>34</sup> s <sup>-1</sup> cm <sup>-2</sup> 300fb E=14TeV BX=25ns <PU>~50			<b>LS3</b>			<b>PostLS3</b> 5x10 <sup>34</sup> s <sup>-1</sup> cm <sup>-2</sup> 3000/fb E=14TeV BX=25ns <PU>~140	
past	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	future				

- High Luminosity (HL) - LHC: upgrade damaged low- $\beta$  triplets and install crab-cavities to optimise bunch overlaps
- $\sqrt{s} = 14$  TeV!
- $L_{inst} = 5 \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$  ( $\rightarrow \sim 10$  times now) i.e.  $L_y = 250 \text{ fb}^{-1} / \text{year}$  ( $L_{total} \sim 3000 \text{ fb}^{-1}$  in 10 years)
- 25ns bunch spacing and  $\langle \text{PileUp} \rangle = 140$  ( $\rightarrow$  now 25)
- Radiation @30 mm from IP:  $2 \times 10^{16} n_{eq} / \text{cm}^2$  ( $\rightarrow \sim 10$  times Phase-I)!
- Dose @30 mm from IP: 10 MGy (1 Grad)!
- Hit rate:  $\sim 2 \text{ GHz} / \text{cm}^2$  ( $\rightarrow \sim 10\text{-}20$  times current one)

**Huge R&D is required to cope with harsh environment**

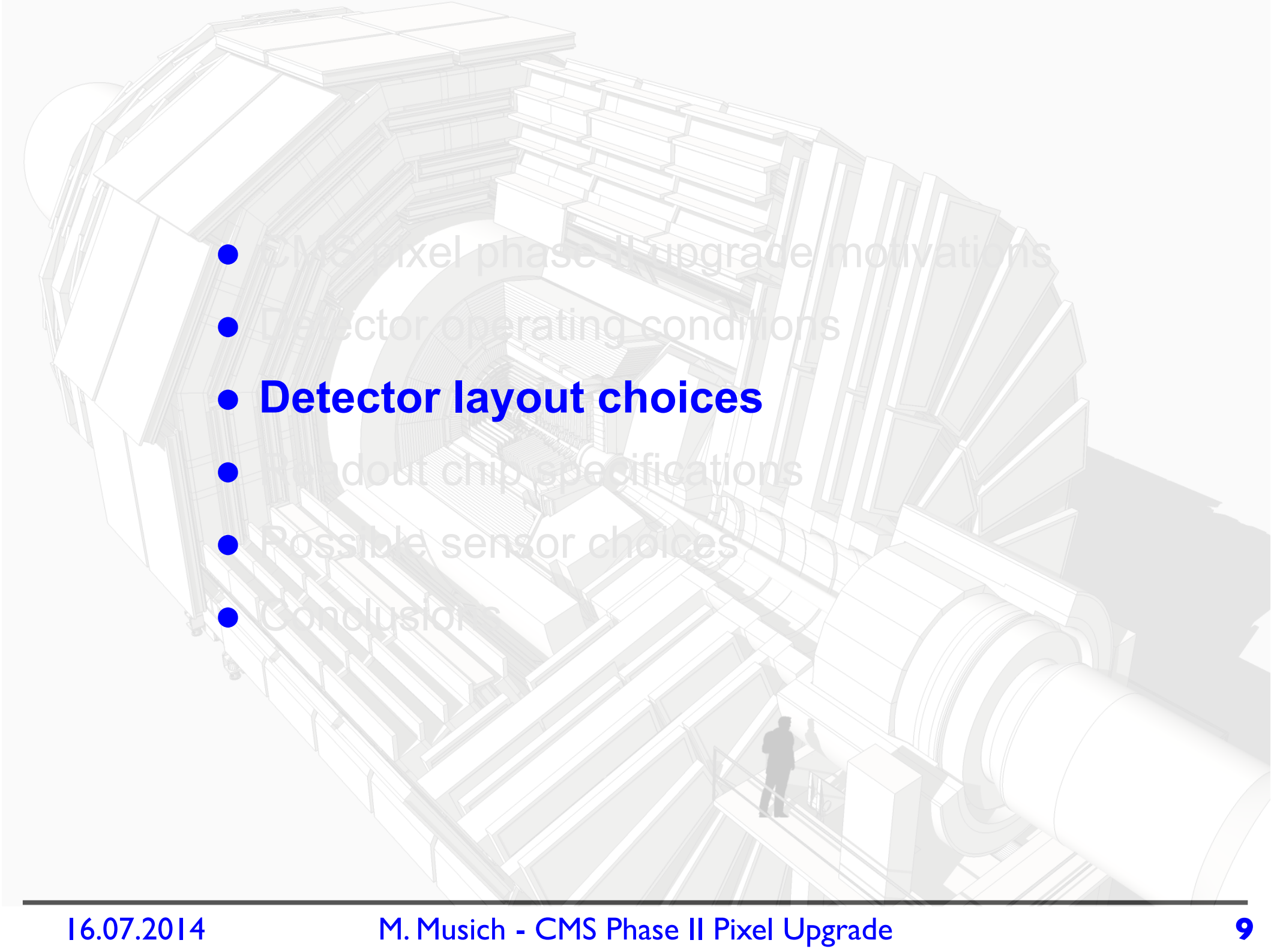


# Pixel Detector operating conditions



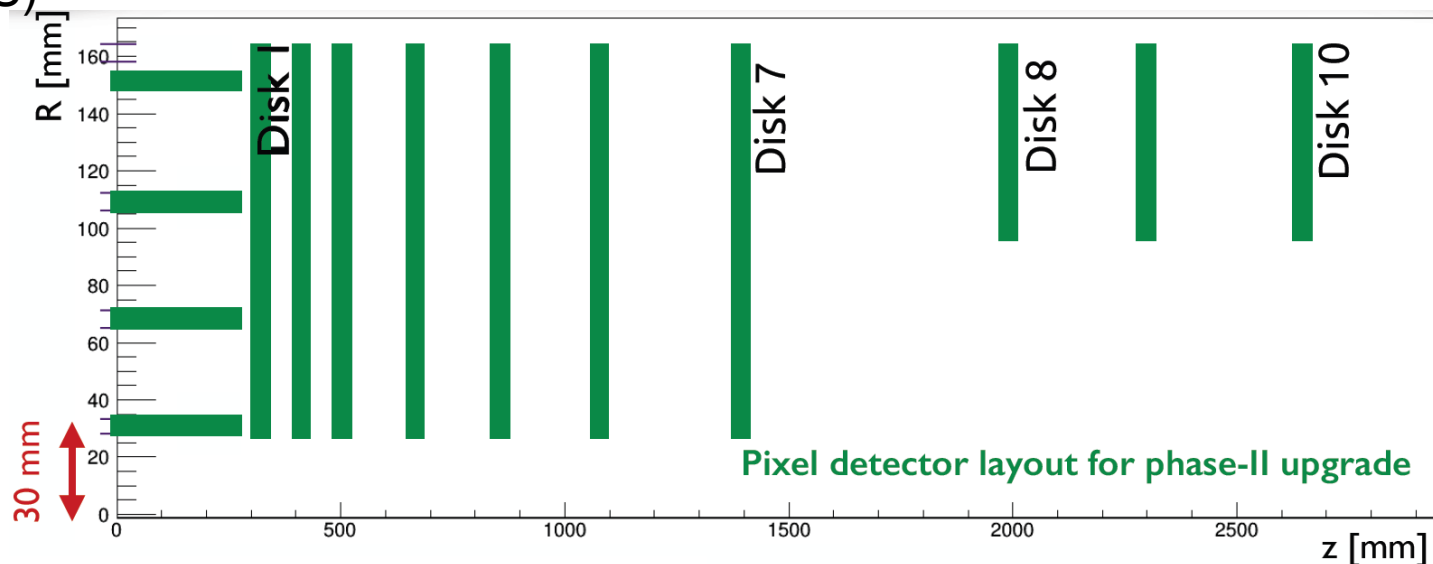
- Overall tracking performance degradation with ageing:
  - After 500 fb<sup>-1</sup> impact parameter degradation of more than 50%;
  - $\langle \text{PU} \rangle = 140$  imply an irreducible data loss of  $\sim 7\%$ .
- Effects on the physics program:
  - Efficiency loss diminishes effectiveness of high- $p_T$  lepton isolation, and degrades jet energy and missing transverse energy resolution!
  - Fake tracks cause biases and resolution degradation in jet energy measurements, increase background levels, and adversely affect high- $p_T$  lepton isolation criteria.



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  - **Detector layout choices**
  - Readout chip specifications
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# Pixel detector layout choices

- **Improve resolution at high- $p_T$**  and improve two-track separation → **increase granularity**  
(present tracker has degraded track finding performance in high-energy jets due to hit merging in the pixel detector)
- **Improve resolution at low- $p_T$**  and reduce secondary interactions → **reduce material**
- **Increase forward acceptance** (to cover peak production region of jets from Vector Boson Fusion and VBS, among highest priorities of the physics program, by mitigating PU effects in jet-ID and energy measurement)
  - 4 barrel layers (→ 3 layers now)
  - 10+10 forward disks, covering up to  $\eta \simeq 4$  (2+2 disks now, up to  $\eta \simeq 2.4$ )
- **Preserve “ease-to-access” of current detector** (possibility to replace degraded parts during TS)



# Basic Pixel Detector design concepts

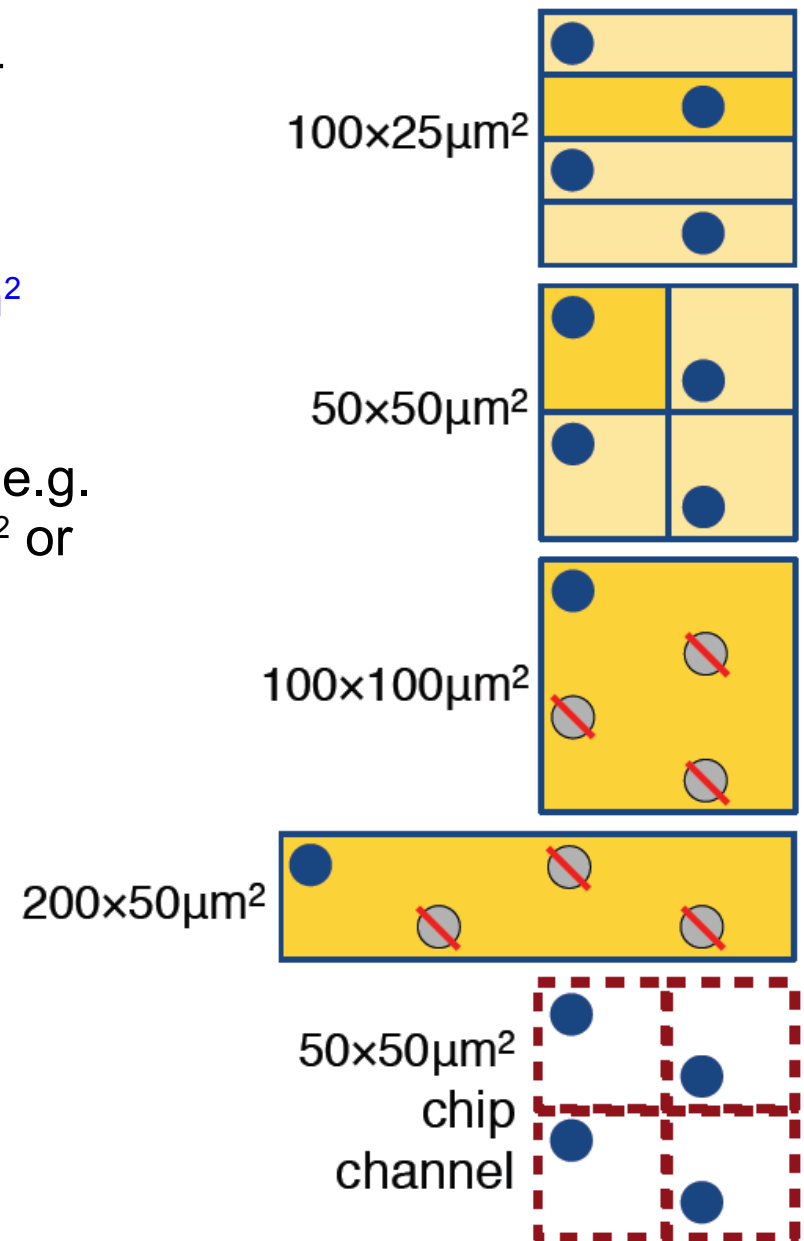
## Sensor pixel cell size:

- Aim to large chip:  $\sim 20 \times 20 \text{ mm}^2$  (current FEI4 dimensions)
- Readout chip channel size:  $50 \times 50 \mu\text{m}^2$
- Target sensor cell:  $50 \times 50 \mu\text{m}^2$  or  $25 \times 100 \mu\text{m}^2$
- Staggered bumps:
  - possibility to switch off 1/2 or 3/4 pixels (e.g. outer regions with pixels of  $100 \times 100 \mu\text{m}^2$  or  $50 \times 200 \mu\text{m}^2$ )

## Readout chip:

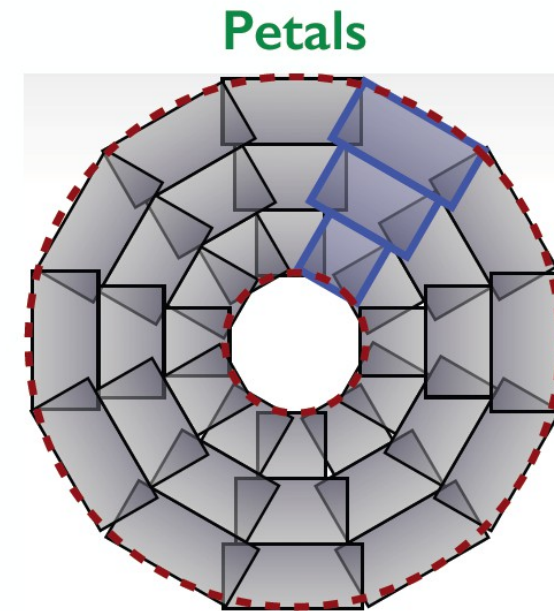
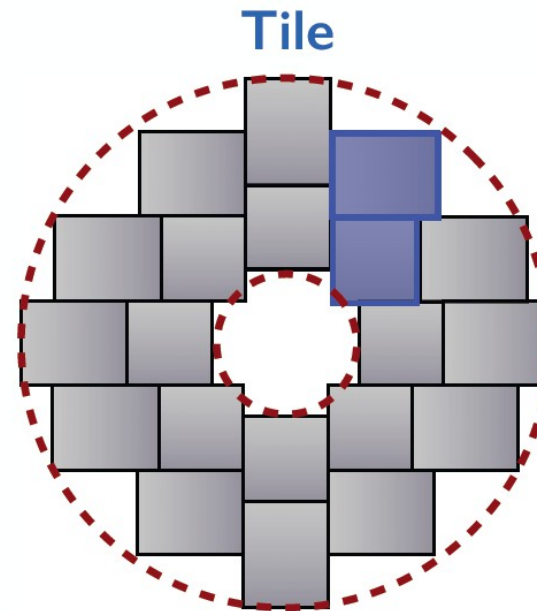
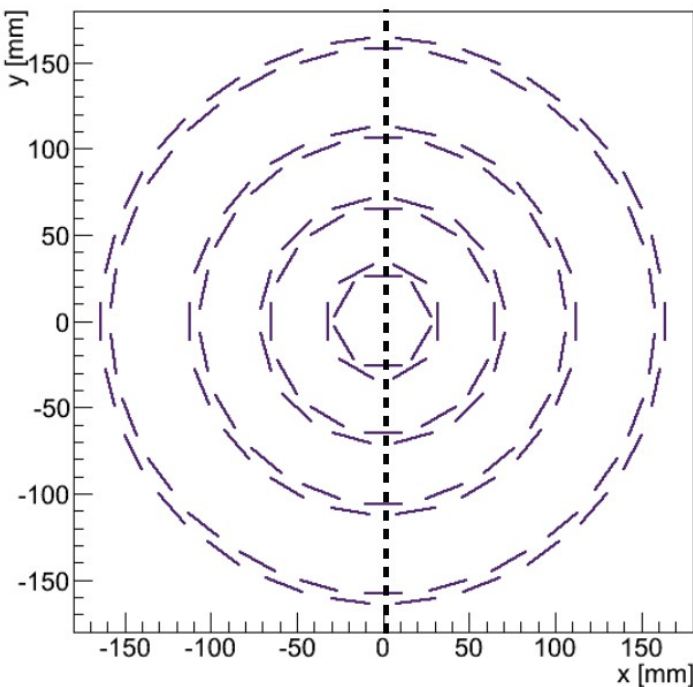
- Candidate technology:  $65 \text{ nm}$  CMOS (RD-53 cross-collaboration Atlas-CMS for development)

*Total active area  
 $\sim 4 \text{ m}^2$  (1.5 x Phase1)*



# Pixel Detector Layout studies

- **Barrel Geometry:** two module types with 4x2 or 4x1 chips and *no projective hole at z=0*
- **Forward Geometry:** two possible coverage schemes considered

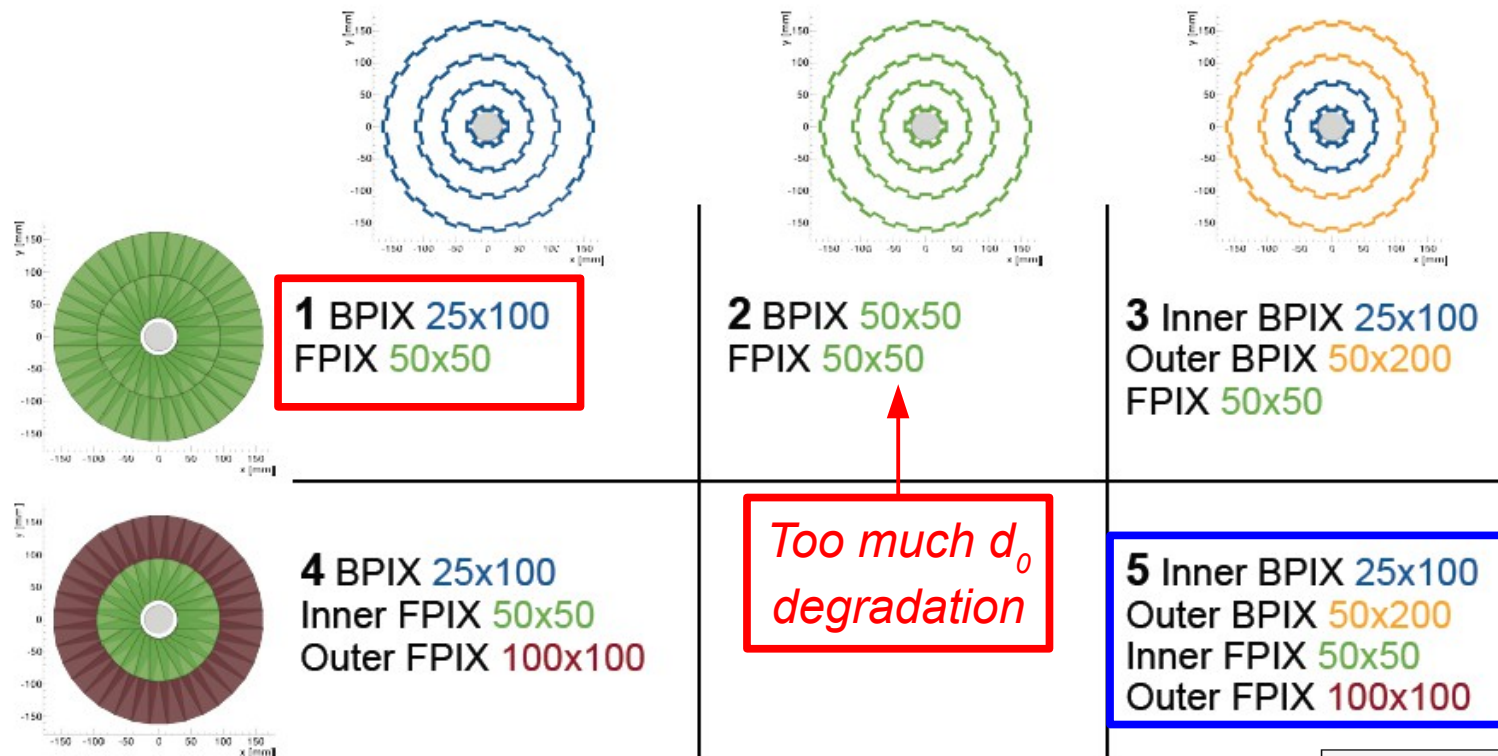


- **Numbers/layer**
- Tile modules: 4x2, 4x1, 2x2
- Petal modules: 4x2, 2x1
- **Chip size 21x23 mm<sup>2</sup> active area**

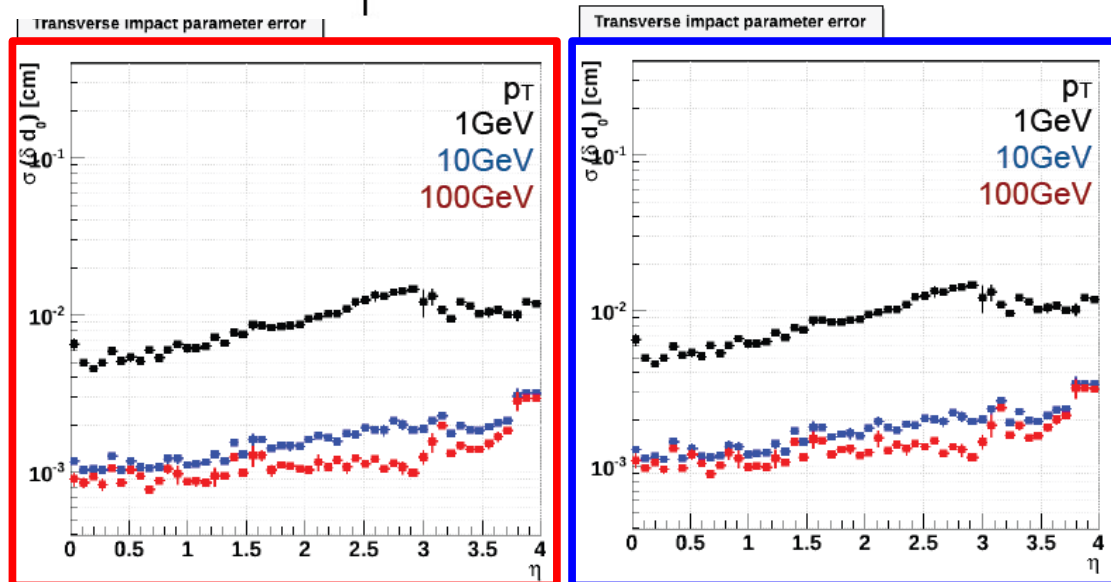
Geometry	Coverage	Overlap	# modules	# chips
Tiles	89%	12%	26	160
Petals	98%	45%	44	232

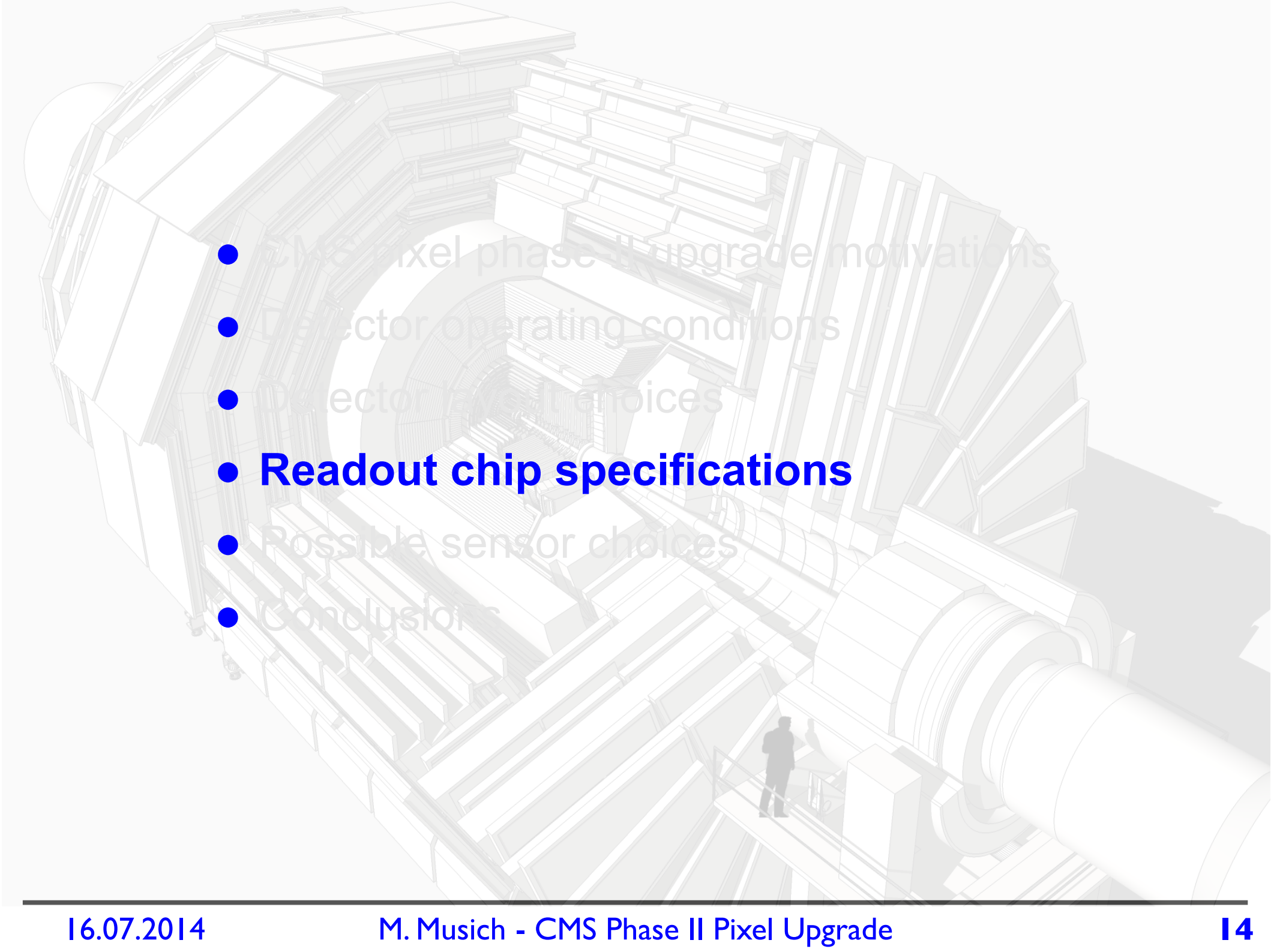


# Pixel detector layout studies



- Pixel cell size studies
- *Too much  $d_0$  degradation with pure squared pixels in BPIX;*
- Two extreme configurations, **#1** and **#5**, have comparable tracking performance;
- Config. **#5** has  $\sim 1/2$  channels of **#1**!



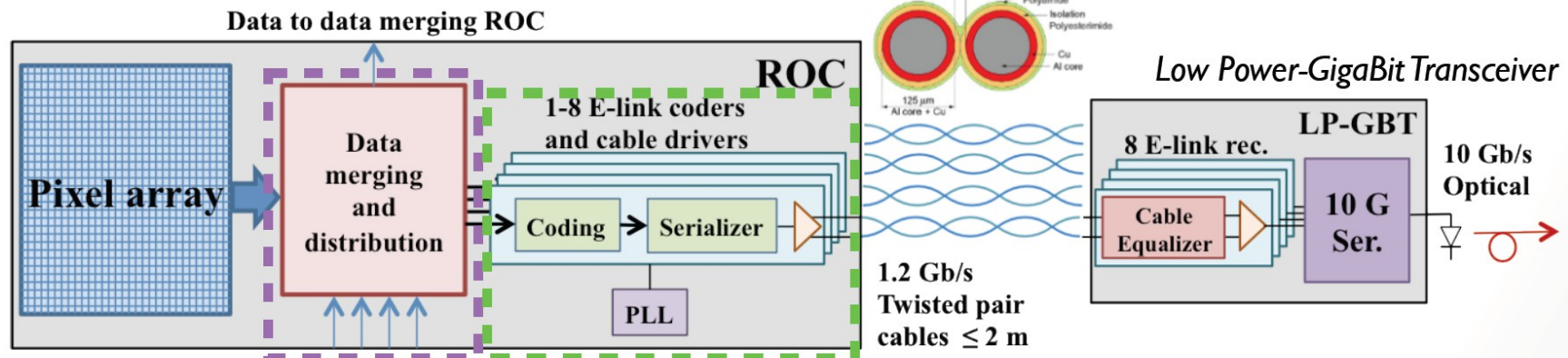
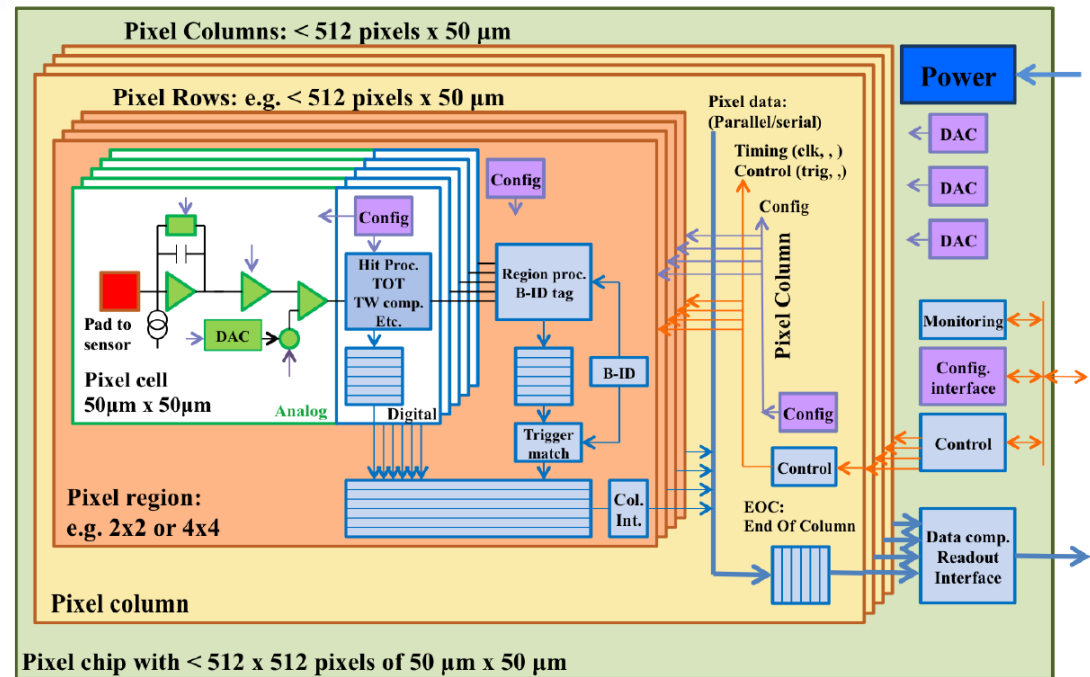
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# Pixel Readout Chip specifications

Generation	Present	Phase-I	Phase-II
<i>Pixel size</i>	100x150 $\mu\text{m}^2$	100x150 $\mu\text{m}^2$	50x50 (25x100) $\mu\text{m}^2$
<i>Sensor, Thickness</i>	2D, 285 $\mu\text{m}$	2D, 285 $\mu\text{m}$	thin 2D, 3D
<i>Chip size</i>	8x10mm <sup>2</sup>	8x10mm <sup>2</sup>	> 20x10 mm <sup>2</sup>
<i>Transistor</i>	1.3x10 <sup>6</sup>		~10 <sup>9</sup>
<i>Hit rate</i>	100 MHz / cm <sup>2</sup>	400 Mhz/ cm <sup>2</sup>	<b>~ 2 GHz / cm<sup>2</sup></b>
<i>Hit memory per chip</i>	0.1 Mb	1 Mb	<b>~ 16 Mb</b>
<i>Trigger rate</i>	100 kHz	100 kHz	<b>~ 1 MHz</b>
<i>Trigger latency</i>	3.2 $\mu\text{s}$	3.2 $\mu\text{s}$	~ 12 $\mu\text{s}$
<i>Readout rate</i>	40 Mb/s	400 Mb/s	~ 2 Gb/s
<i>Radiation</i>	15 Mrad, r=42 mm L = 150 fb <sup>-1</sup>	120 Mrad, r=29 mm, L = 500 fb <sup>-1</sup>	<b>1 Grad, r=30mm, L = 3000 fb<sup>-1</sup></b>
<i>Technology</i>	250 nm	250 nm	<b>65 nm</b>
<i>Architecture</i>	Analog	Digital	Digital
<i>Buffer location</i>	End of Column	End of Column	Pixel
<i>Power</i>	~ 0.15 W/ cm <sup>2</sup>	~ 0.15 W / cm <sup>2</sup>	~ 0.3 – 0.5 W / cm <sup>2</sup>

# Pixel readout chip and data link specifications

- Possibility to tune bias currents of analogue front-end to account for different sensor choices
- Digital hit processing, including trigger latency buffer, implemented in pixel regions (e.g. 2x2 or 4x4pixels) followed by data merging, formatting and readout after the first level trigger accept (*price of local digital processing: digital noise injection into the front end to be controlled. Clocks and trigger signals must be distributed throughout the pixel matrix*)



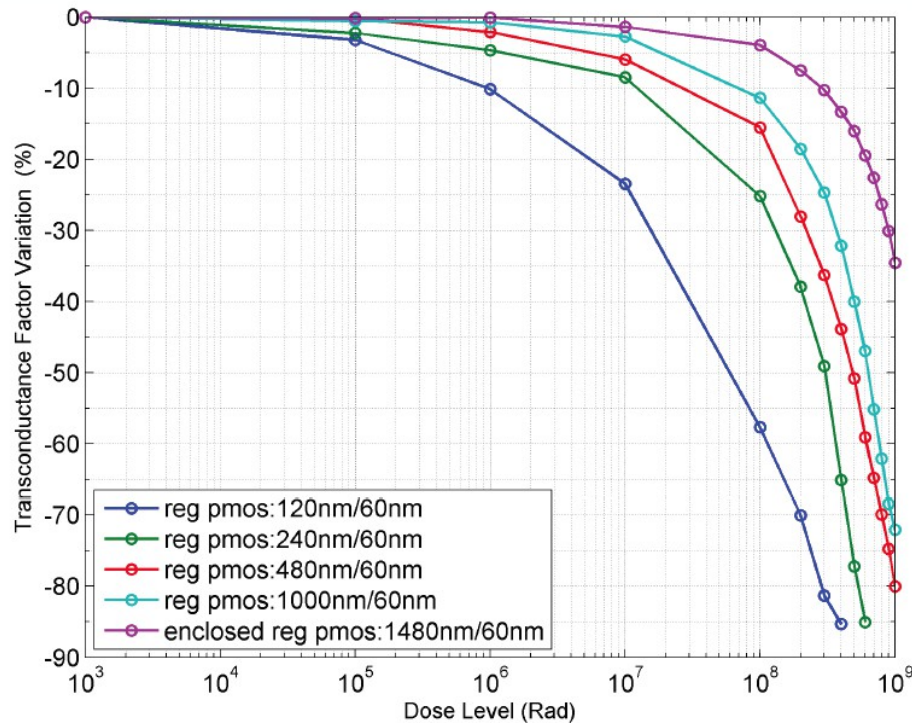
The chip will also implement data merging functionality (from 2 or even 4 chips in the innermost region)

The chip should provide up to 8 data output e-links of 1.3 Gb/s

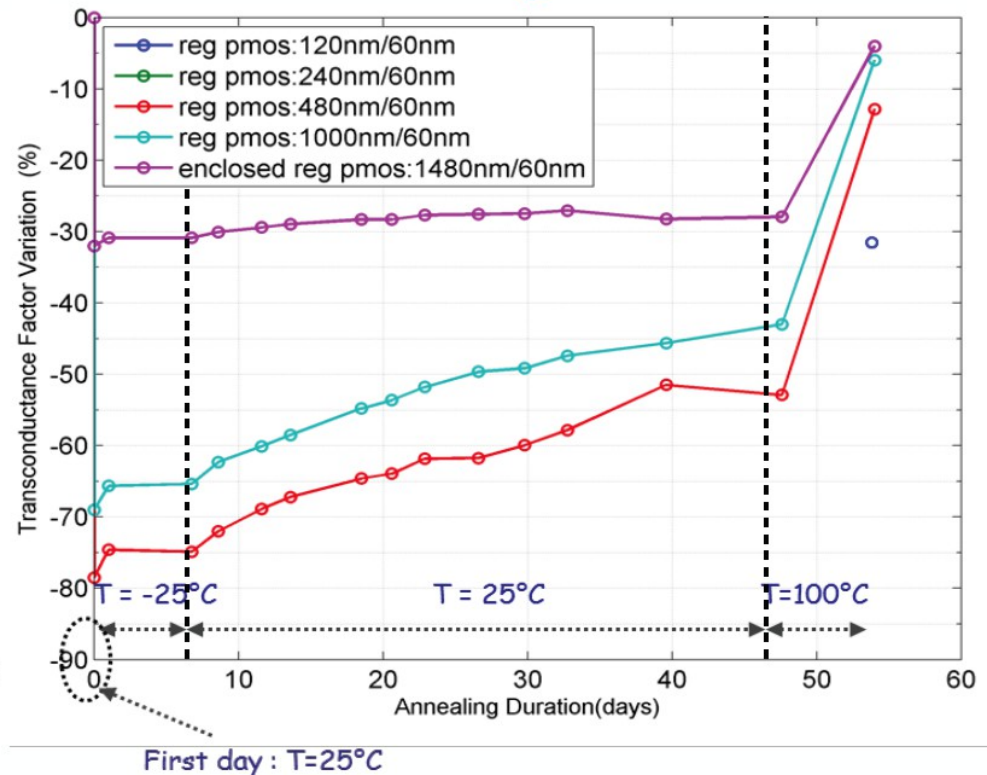


# Radiation hardness of 65 nm CMOS technology

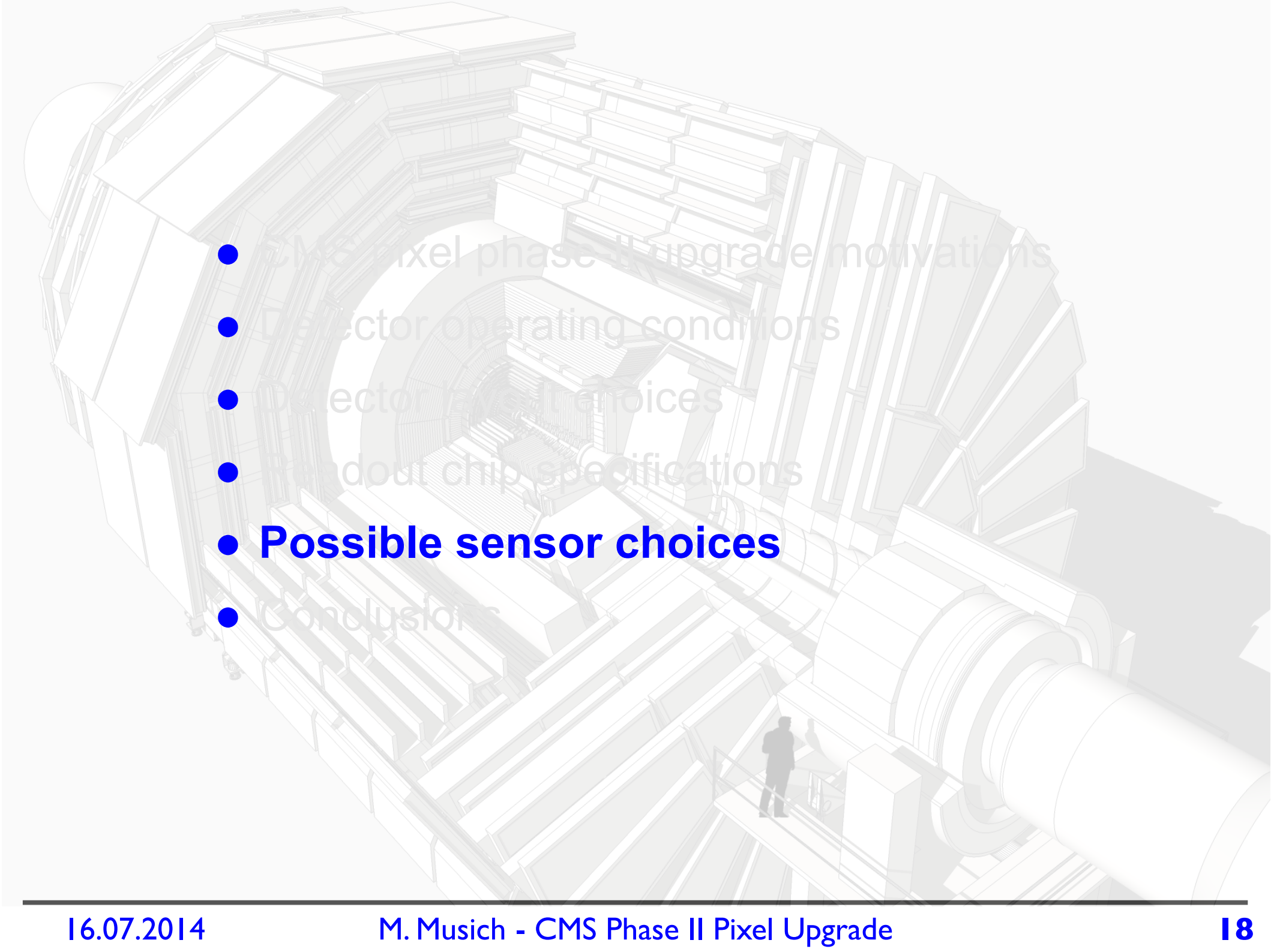
Transconductance factor variation vs dose



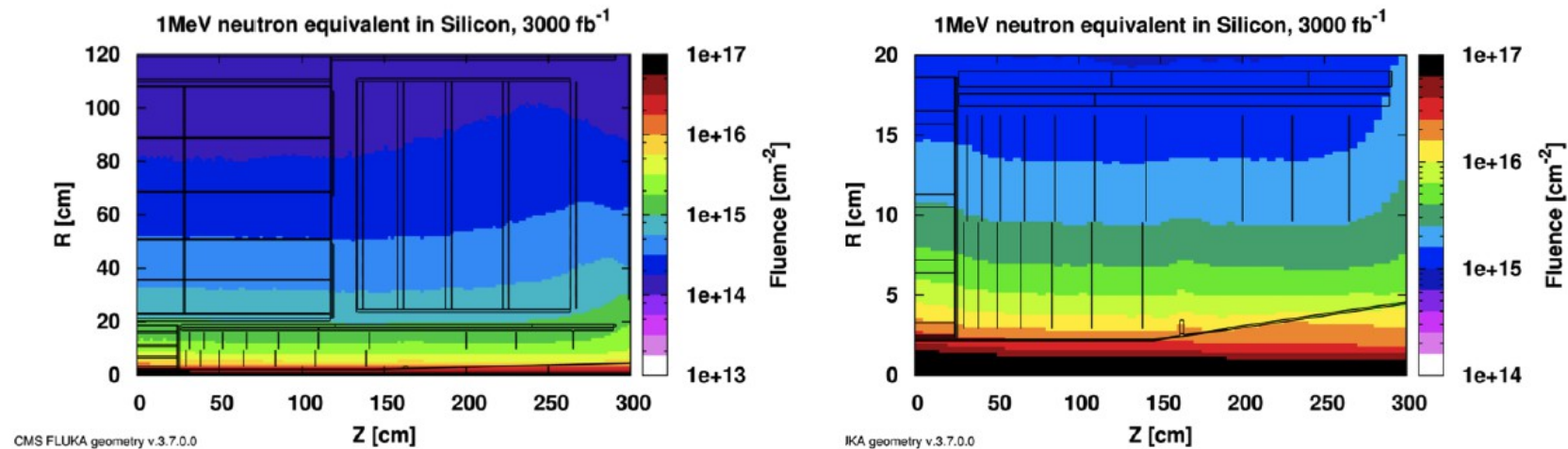
Transconductance factor var. vs annealing time



- Among other effects, PMOS-FETs (especially minimum size ones) show **large transconductance degradation** vs. dose (becomes very steep at dose > 100 Mrad)
- Damage mechanism have yet to be fully understood
- It appears that some of the radiation damage in the chip could be **annealed with high temperatures** → possibly define plausible annealing scenarios during detector maintenance to optimise longevity of sensors and electronics (detailed evaluation of annealing effects on sensor performance)

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# Possible sensor choices

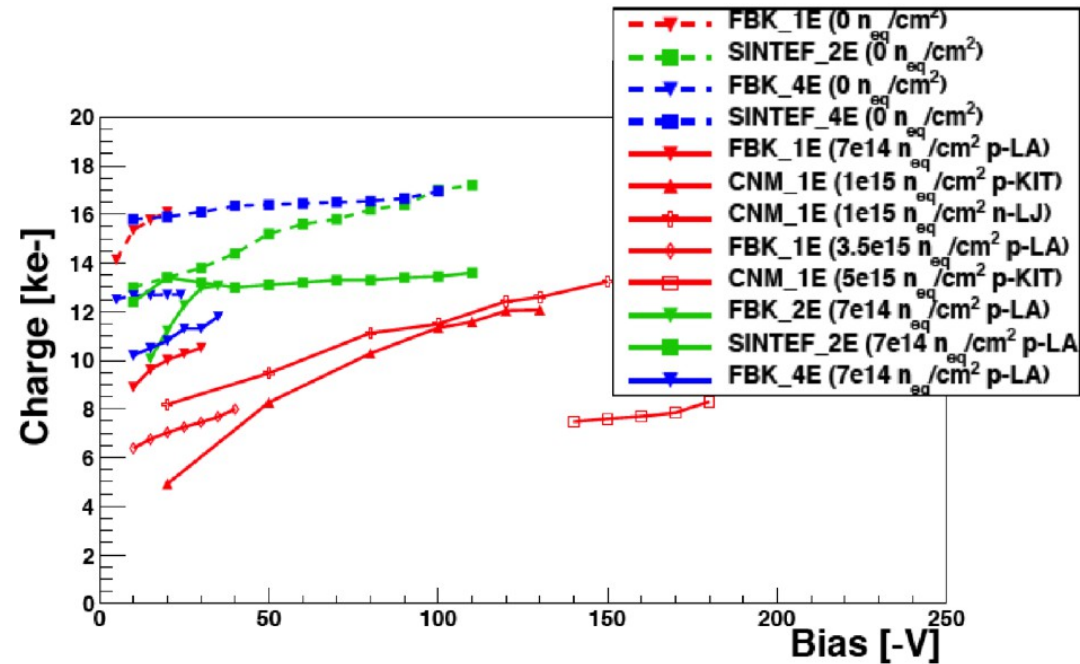
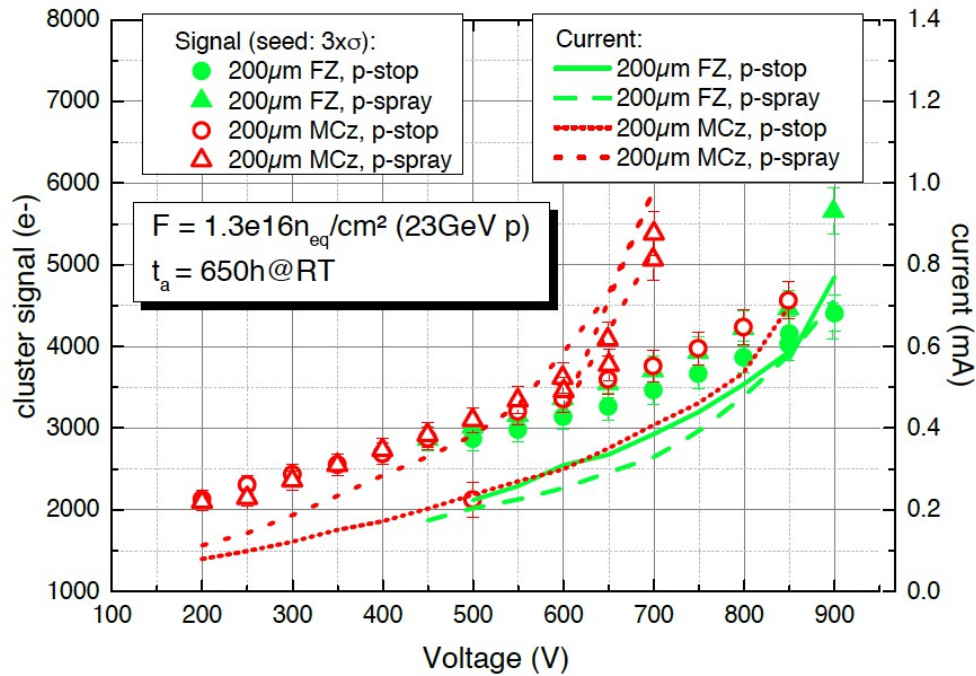


Radiation tolerance dominates technological choice for sensors. Possible sensors technologies:

- Favoured technology: **planar Silicon**
  - Define suitable *n-in-p* process and design (more cost effective than present *n-in-n*)
  - Thin thickness
  - Requires robust spark rejection material
- Alternative/complementary for innermost layer: **3D Silicon**
  - Intrinsically higher radiation resistant (the shorter charge collection distance);
  - production process more expensive and not suitable for large volumes, use of 3D sensors could be limited to the small regions of highest particle fluence;
  - Define suitable sensor thickness and electrode geometry
  - Address production issues (e.g. yield and cost)



# Possible sensor choices



- Signal charge and leakage current in **planar n-in-p silicon pixel structures** in different processes and isolations (irradiation  $1.3 \times 10^{16} n_{eq} / cm^2$ )

- Signal charge in **3D n-in-p silicon pixel structures** from different vendors and with different column configurations (before and after irradiation up to  $3.5 \times 10^{15} n_{eq} / cm^2$ )

## Need to define:

- Sensor thickness
- Sensor process (FZ, MCz, EPI)
- Spark rejection material
- Pixel isolation and bias scheme

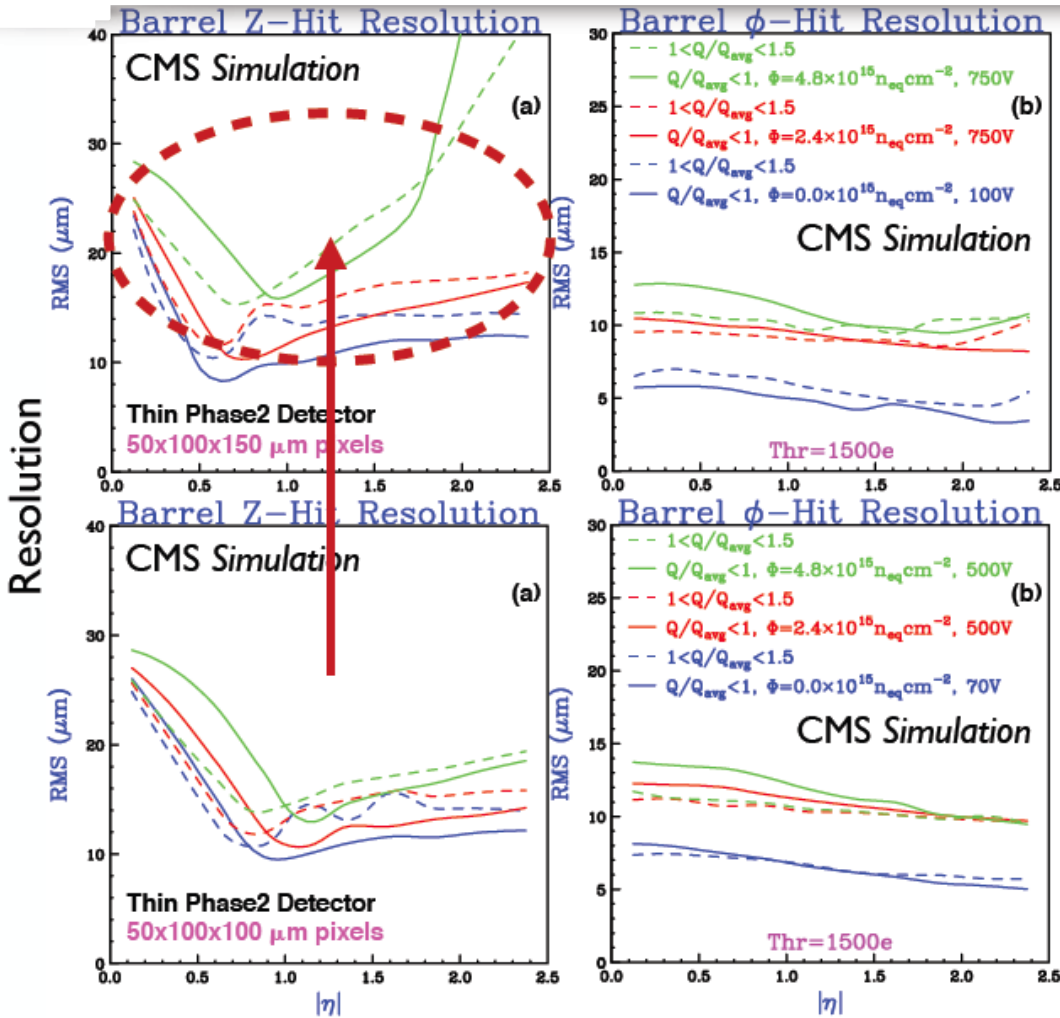
## Need to define:

- Column electrodes positions and size  
→ sensor thickness
- Production process: single/double sided



# Thin planar Silicon sensors: thin thickness

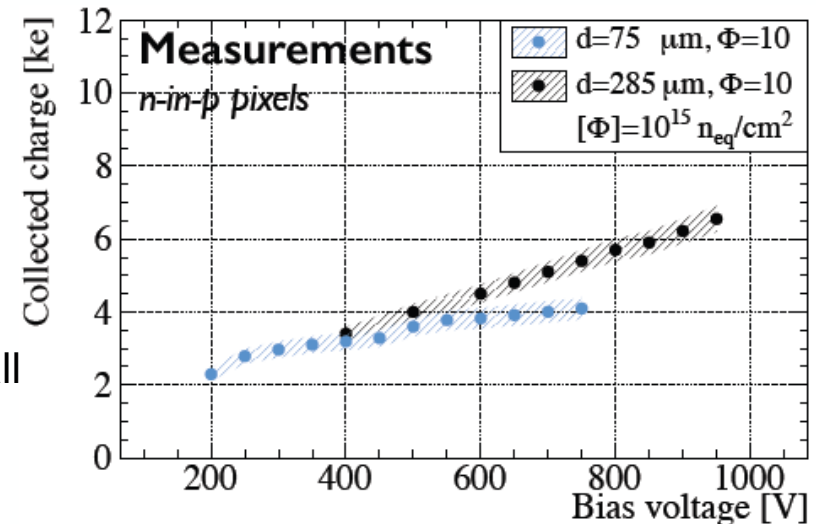
## Barrel resolutions



Assumptions:

- Noise  $150 e^-$  and other readout and calibration effects are small
- Extrapolate irradiated Silicon model, tuned on data up to  $1.2 \times 10^{15} \text{ neq} / \text{cm}^2$  to larger fluence,  $4.8 \times 10^{15} \text{ neq} / \text{cm}^2$
- Average E-fields of 50 kV / cm can be achieved

- Thin planar sensors advantages:
  - Higher fields with same bias  $\rightarrow$  shorter drift time  $\rightarrow$  less trapping  $\rightarrow$  ultimately, better radiation hardness
  - Reduced full-depletion voltage
  - Smaller clusters  $\rightarrow$  reduce merged cluster fraction in dense jets
- At very high fluences **thick** and **thin** planar sensors give similar charge



# Conclusions

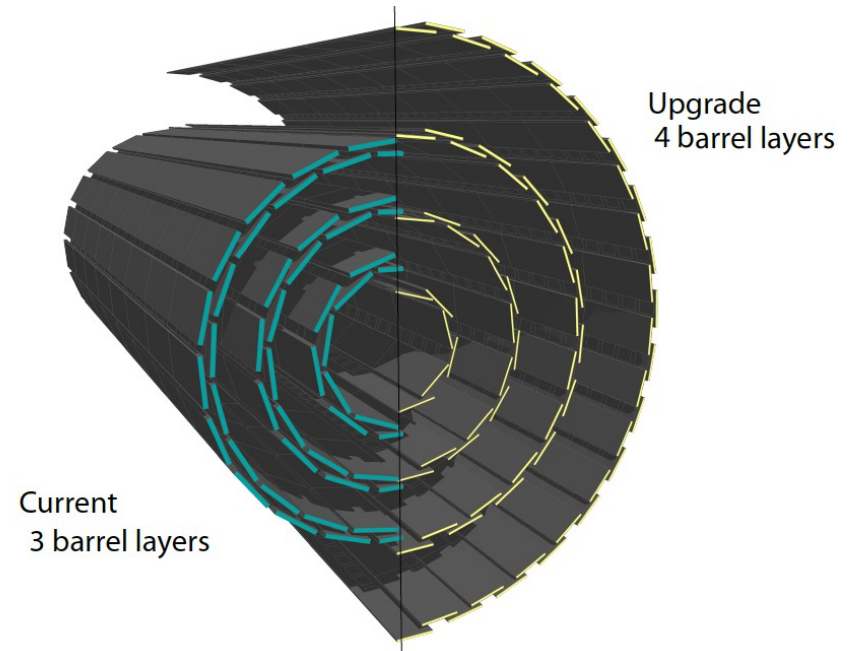
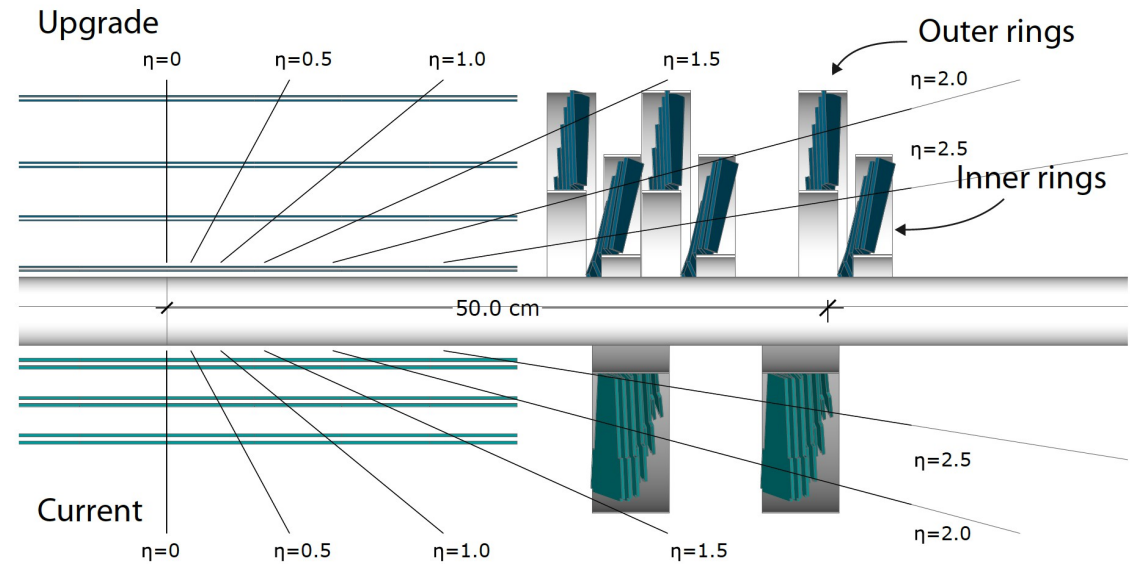
- Pixel detector operating conditions during Phase-II are extremely challenging
  - Pile-Up = 140
  - Radiation @ 30 mm from IP:  $2 \times 10^{16} n_{eq} \text{ cm}^2$
  - Dose @ 30 mm from IP: 10 MGy (1Grad)
  - Hit rate  $\sim 2 \text{ GHz/ cm}^2$
- Final detector layout and geometry is under definition
- Redout chip development (Atlas-CMS collaboration): 65 nm candidate technology  $\rightarrow$  need to demonstrate radiation hardness up to foreseen 10 years operation at HL-LHC
- Sensor development: Silicon thin planar n-in-p (and/or Silicon 3D for innermost layer) candidate technology  $\rightarrow$  need to define sensor process, bias isolation geometry, thickness, electrode geometry.

**Still a lot of work ahead (hopefully) leading to future physics discoveries!**

# Backup

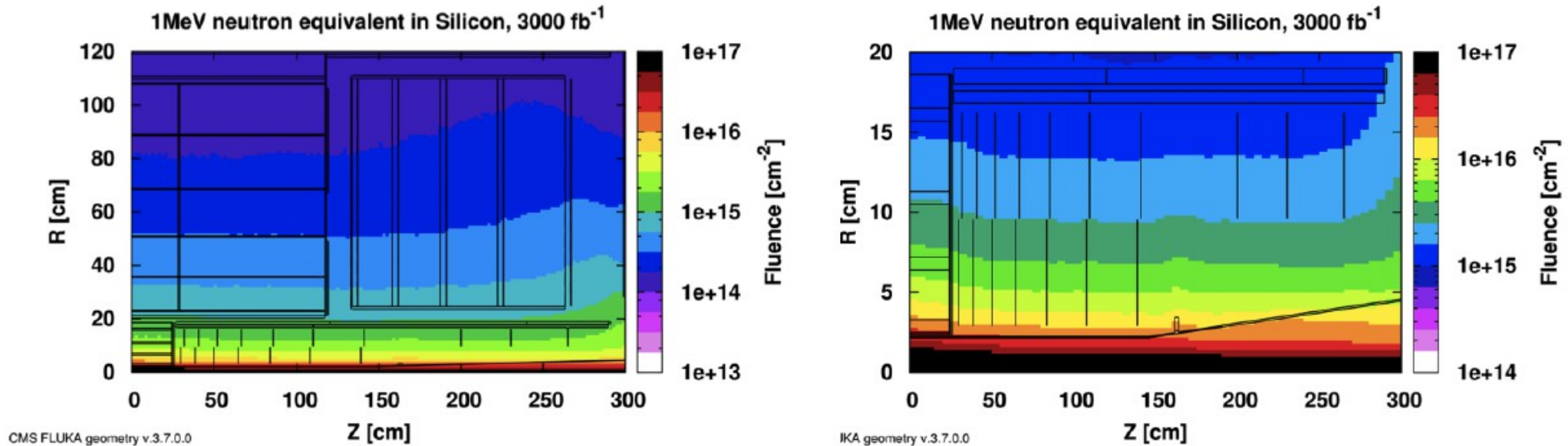
# Phase I - post 2017 Pixel Detector

- The Phase1 pixel detector is an improved version of the current pixel detector.
- 4 layers / 3+3 disks (100x150  $\mu\text{m}^2$ , n<sup>+</sup>-in-n): improved track resolution and efficiency
- New readout chip: reduced dynamic inefficiency at high rate and PU
- Reduced material: CO<sub>2</sub> cooling, new cabling and DC-DC powering scheme
- Will be installed during the 2016 Technical Stop; a pilot disk 3 blade is being installed for 2015 for testing



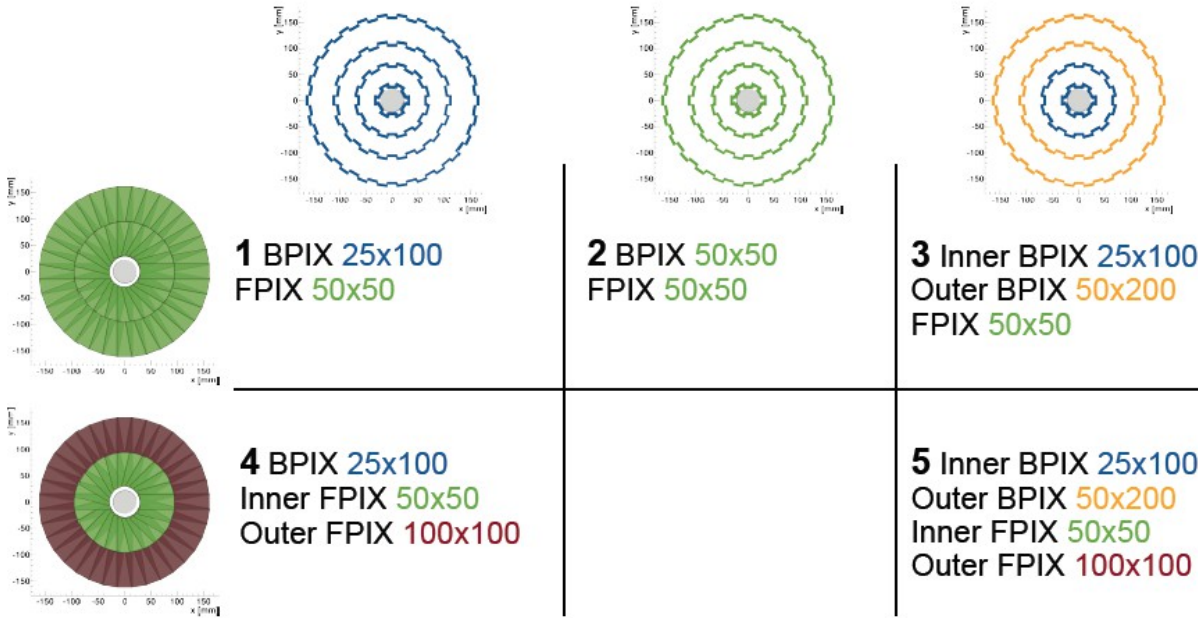


# Fluences

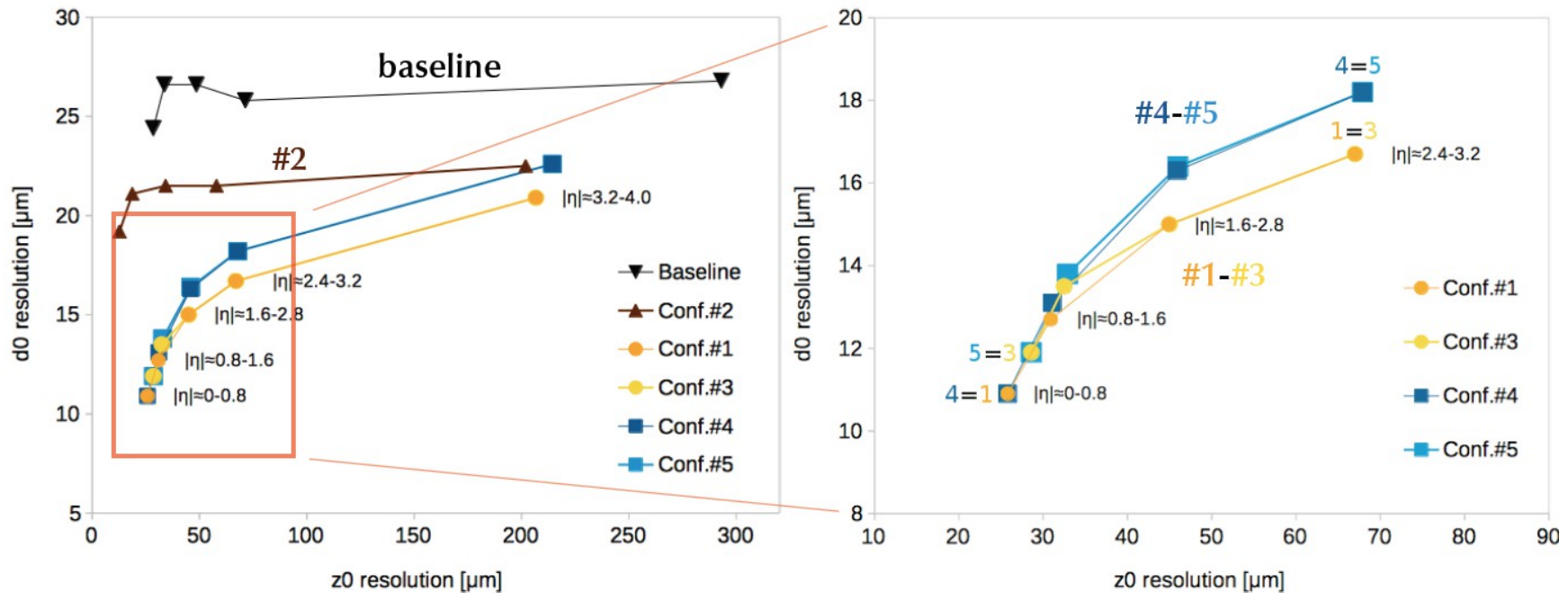


- Left: map of the expected particle fluence in the Tracker volume corresponding to an integrated luminosity of 3000 fb<sup>-1</sup>, expressed in terms of 1 MeV neutron equivalent fluence.
- Right: detail of the fluence in the pixel volume. The expected fluence has a strong dependence on radius, while it is almost independent of the z coordinate.

# Impact parameters resolutions $d_0$ vs $z_0$



- **Petal** configurations with mixed pixel sizes show better tracking performance than **Petal #2** and baseline (Phase-I) geometries



# Phase-I Tracking Performance

